

# ISA1989AU1

FOR LOW FREQUENCY AMPLIFY APPLICATION  
SILICON PNP EPITAXIAL TYPE(ULTRA SUPER MINI TYPE)

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## DESCRIPTION

ISA1989AU1 is a ultra super mini package resin sealed silicon PNP epitaxial transistor, It is designed for low frequency voltage application.

## FEATURE

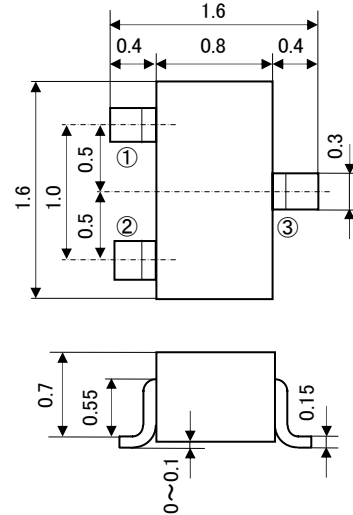
- Small collector to emitter saturation voltage.  
VCE(sat)=-0.3V max(@ I<sub>C</sub>=-30mA, I<sub>B</sub>=-1.5mA)
- Excellent linearity of DC forward gain.
- Super mini package for easy mounting

## APPLICATION

For Hybrid IC, small type machine low frequency voltage Amplify application.

## OUTLINE DRAWING

Unit: mm



JEITA: SC-75A

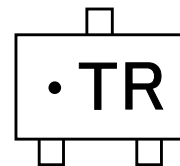
## TERMINAL CONNECTER

- ①: BASE
- ②: EMITTER
- ③: COLLECTOR

## MAXIMUM RATINGS (T<sub>a</sub>=25°C)

Symbol	Parameter	Ratings	Unit
V <sub>CBO</sub>	Collector to Base voltage	-50	V
V <sub>CEO</sub>	Collector to Emitter voltage	-50	V
V <sub>EBO</sub>	Emitter to Base voltage	-6	V
I <sub>O</sub>	Collector current	-100	mA
P <sub>c</sub>	Collector dissipation	150	mW
T <sub>j</sub>	Junction temperature	+150	°C
T <sub>stg</sub>	Storage temperature	-55 ~ +150	°C

## MARKING



## ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C)

Parameter	Symbol	Test conditions	Limits			Unit
			Min	Typ	Max	
C to E break down voltage	V(BR) <sub>CEO</sub>	I <sub>C</sub> =-100 μA, R <sub>BE</sub> =∞	-50	-	-	V
Collector cut off current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0mA	-	-	-0.5	μA
Emitter cut off current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0mA	-	-	-0.5	μA
DC forward current gain	hFE	V <sub>CE</sub> =-6V, I <sub>C</sub> =-1mA	120	-	560	
DC forward current gain	hFE	V <sub>CE</sub> =-6V, I <sub>C</sub> =-0.1mA	70	-	-	
C to E Saturation Voltage	VCE(sat)	I <sub>C</sub> =-30mA, I <sub>B</sub> =-1.5mA	-	-	-0.3	V
Gain bandwidth product	fT	V <sub>CE</sub> =-6V, I <sub>E</sub> =10mA	-	200	-	MHz
Collector output capacitance	Cob	V <sub>CE</sub> =-6V, I <sub>E</sub> =0, f=1MHz	-	2.5	-	pF

※) It shows hFE classification in below table.

Item	Q	R	S
hFE item	120~270	180~390	270~560

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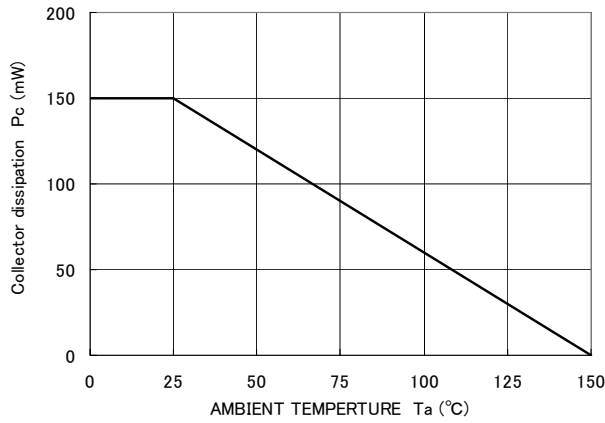
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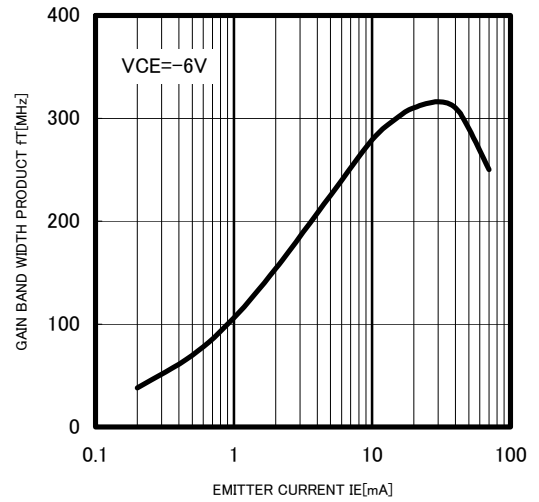
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## TYPICAL CHARACTERISTICS

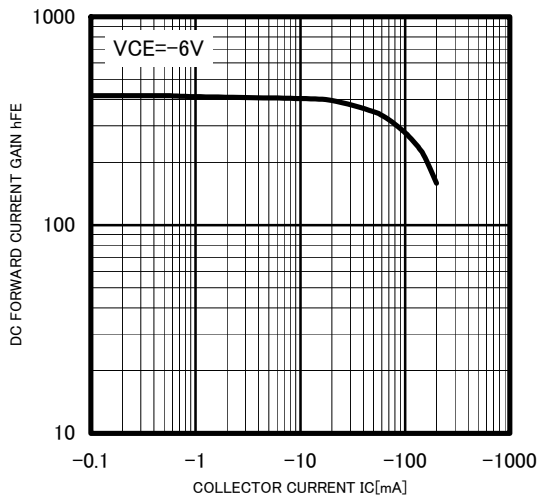
Collector dissipation — AMBIENT TEMPERATURE



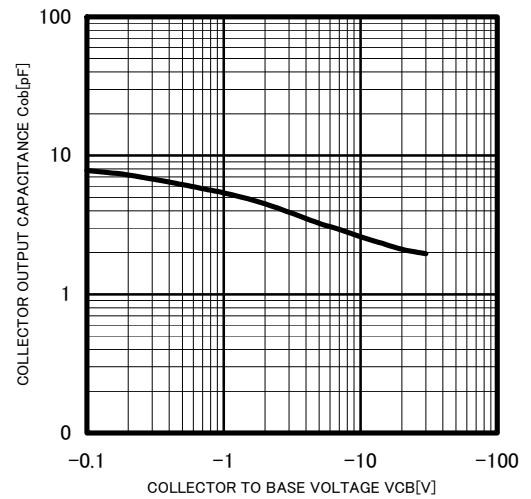
GAIN BAND WIDTH PRODUCT VS. EMITTER CURRENT



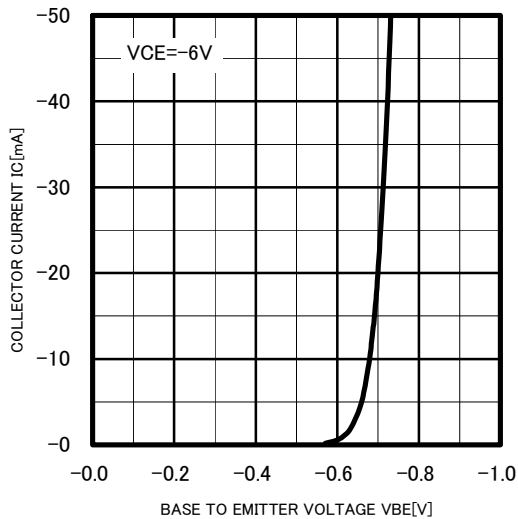
DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE



COMMON EMITTER TRANSFER





*Marketing division, Marketing planning department*

6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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